AMENDMENTS TO THE CLAIMS

The following listing of claims will replace all prior versions and listings of claims in the application.

LISTING OF CLAIMS

- 1-2. (CANCELLED)
- (ORIGINAL) A semiconductor device comprising:

a first semiconductor package having a plurality of first lands that have different thicknesses from each other; and

second semiconductor packages, each having a plurality of second lands that have different thicknesses from each other, the second lands being arranged opposite the first lands.

- 4. (ORIGINAL) The semiconductor device according to claim 3, wherein the thickness of each of the first lands and the second lands gradually increases as a space between the first semiconductor package and the second semiconductor packages increases.
- 5. (ORIGINAL) The semiconductor device according to claim 3, further including bumps bonded to the lands.
- 6. (ORIGINAL) The semiconductor device according to claim 5, wherein the bumps have substantially the same volume.

7. (ORIGINAL) The semiconductor device according to claim 3, further including:

insulating films formed on the lands; and

openings that are formed in the insulating films and have different opening areas corresponding to the thicknesses of the lands.

- 8. (ORIGINAL) The semiconductor device according to claim 7, wherein the opening areas of the openings decrease as the thicknesses of the lands increase.
 - 9. (ORIGINAL) The semiconductor device according to claim 3, wherein: the first semiconductor package includes:
 - a first carrier substrate having the first lands; and
- a first semiconductor chip that are flip-chip mounted to the first carrier substrate, and

the second semiconductor packages includes:

second carrier substrates having the second lands;

second semiconductor chips mounted to the second carrier substrates;

bumps for bonding the first lands and the second lands to hold an end of

each of the second carrier substrates directly above the first semiconductor chip; and

seals for sealing the second semiconductor chips.

10. (ORIGINAL) The semiconductor device according to claim 9, wherein the first semiconductor package further comprises a ball grid array package in which the first semiconductor chip is flip-chip mounted to the first carrier substrate, and each of the second semiconductor packages further comprises at least one of a ball grid array package and a chip-size package in which each of the second semiconductor chips mounted to each of the second carrier substrates is sealed by molding.

11. (ORIGINAL) An electronic device comprising:

a first carrier substrate having a plurality of first lands that have different thicknesses from each other;

a first electronic component that is flip-chip mounted to the first carrier substrate; second carrier substrates, each having a plurality of second lands that have different thicknesses from each other, the second lands being arranged opposite the first lands:

second electronic components mounted to the second carrier substrates; and seals for sealing the second electronic components.

12. (ORIGINAL) An electronic apparatus comprising:

a first semiconductor package having a plurality of first lands that have different thicknesses from each other;

second semiconductor packages, each having a plurality of second lands that have different thicknesses from each other, the second lands being arranged opposite the first lands; and

a motherboard having the second semiconductor packages.

13. (CANCELLED) A method for manufacturing a carrier substrate comprising the steps of:

forming a plurality of lands on a first carrier substrate;

forming an insulating film on the plurality of lands formed on the first carrier substrate;

forming openings in the insulating film, wherein the openings have different opening areas and expose the surfaces of the lands; and

varying the thicknesses of the lands by etching the surfaces of the lands through the openings.

14. (CANCELLED) A method for manufacturing a semiconductor device comprising the steps of:

forming a plurality of first lands that have different thicknesses from each other on a first carrier substrate;

mounting a first semiconductor chip to the first carrier substrate;

forming a plurality of second lands that have different thicknesses from each other on second carrier substrates;

mounting second semiconductor chips to the second carrier substrates;

forming bumps on the second lands; and

arranging the second carrier substrates relative to the first carrier substrate by bonding the bumps formed on the second lands to the first lands.

15. (CANCELLED) A method for manufacturing a semiconductor device comprising the steps of:

forming a plurality of first lands on a first carrier substrate;

forming a first insulating film on the plurality of first lands formed on the first carrier substrate;

forming first openings in the first insulating film, wherein the first openings have different opening areas and expose the surfaces of the first lands;

varying the thicknesses of the first lands by etching the surfaces of the first lands through the first openings;

mounting a first semiconductor chip to the first carrier substrate;

forming a plurality of second lands on second carrier substrates;

forming second insulating films on the plurality of second lands formed on the second carrier substrates;

forming second openings in each of the second insulating films, wherein the second openings have different opening areas and expose the surfaces of the second lands;

varying the thicknesses of the second lands by etching the surfaces of the second lands through the second openings;

mounting second semiconductor chips to the second carrier substrates;

forming bumps on the second lands; and

arranging the second carrier substrates relative to the first carrier substrate by bonding the bumps formed on the second lands to the first lands.

16. (CANCELLED) A method for manufacturing an electronic device comprising the steps of:

forming a plurality of first lands that have different thicknesses from each other on a first carrier substrate;

mounting a first electronic component on the first carrier substrate;

forming a plurality of second lands that have different thicknesses from each other on second carrier substrates;

mounting second electronic components on the second carrier substrates;

forming bumps on the second lands; and

arranging the second carrier substrates relative to the first carrier substrate by bonding the bumps formed on the second lands to the first lands.